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Siliup Semiconductor

SP010N70T8

100V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}TYP$	I_D
100V	70m Ω @10V	6A

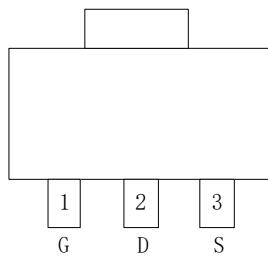
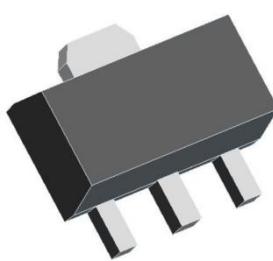
Feature

- High power and current handing capability
- Surface mount package

Application

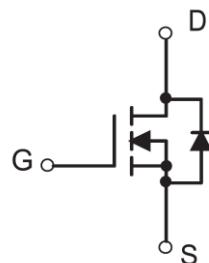
- DC-DC Converters
- Power management functions

Package

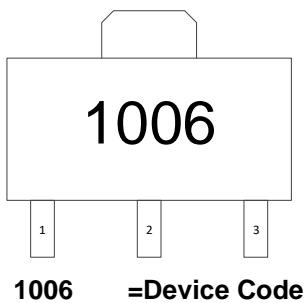


SOT-89-3L

Circuit diagram



Marking





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Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	6	A
Pulsed Drain Current	I _{DM}	24	A
Maximum Power Dissipation	T _A =25°C	P _D	1.5
	T _C =25°C		4.0
Thermal Resistance,Junction-to-Ambient ¹	R _{θJA}	83	°C/W
Thermal Resistance,Junction-to-Case ¹	R _{θJC}	31	
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 To 175	°C

Electrical characteristics (Ta=25 °C, unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V ID=250μA	100	110	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , ID=250μA	1.2	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, ID=5A	-	70	100	mΩ
		V _{GS} =4.5V, ID=3A	-	85	120	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 15V, V _{GS} =0V, f =1MHz	-	1100	-	PF
Output Capacitance	C _{oss}		-	55	-	
Reverse Transfer Capacitance	C _{rss}		-	40	-	
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{GS} =10V, V _{DD} =50V, RG = 3Ω, ID= 5A	-	3.9	-	nS
Turn-on Rise Time	t _r		-	26	-	
Turn-Off Delay Time	t _{d(off)}		-	16.2	-	
Turn-Off Fall Time	t _f		-	8.9	-	
Total Gate Charge	Q _g	V _{GS} = 10V, V _{DS} = 50V, ID=5A	-	12	-	nC
Gate-Source Charge	Q _{gs}		-	2.9	-	
Gate-Drain Charge	Q _{gd}		-	1.8	-	
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,IS=1A	-	-	1.2	V
Diode Forward Current	I _s		-	-	6	A



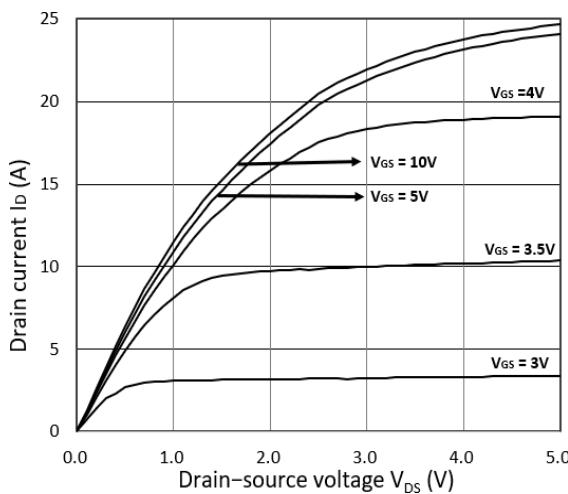
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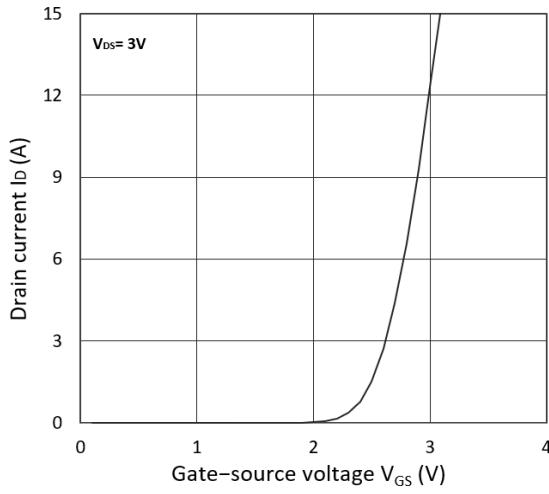
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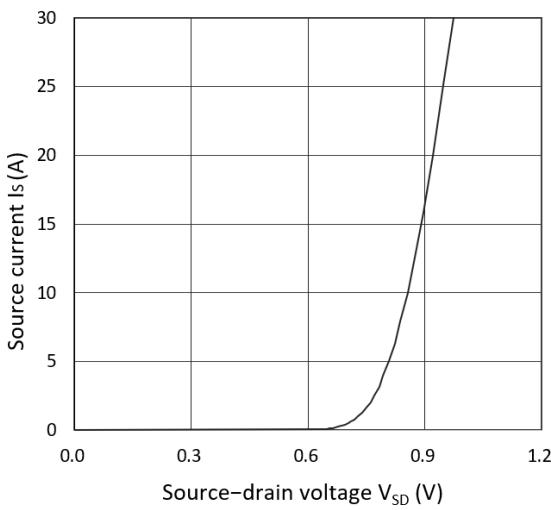
Typical Characteristics



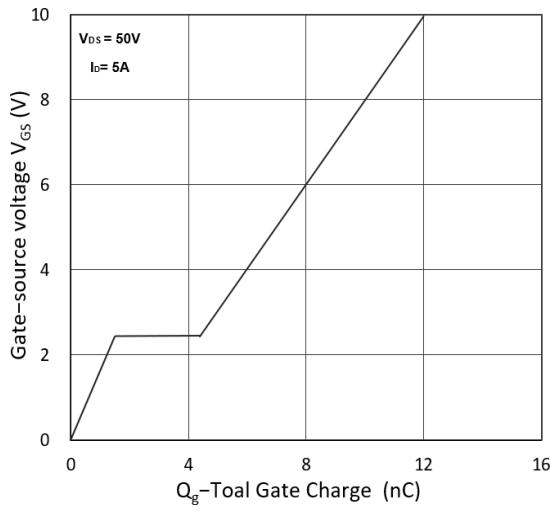
Output Characteristics



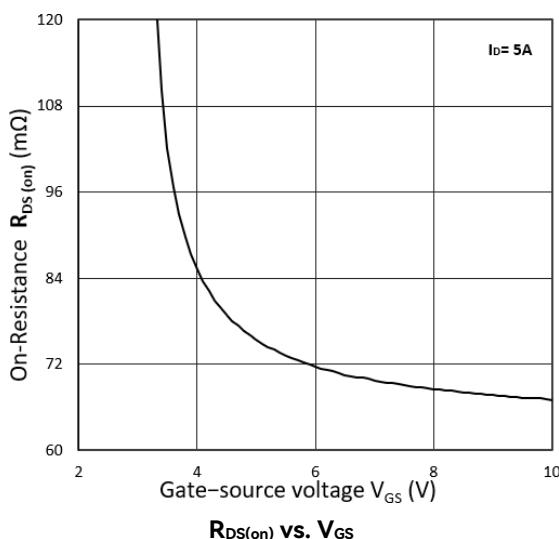
Transfer Characteristics



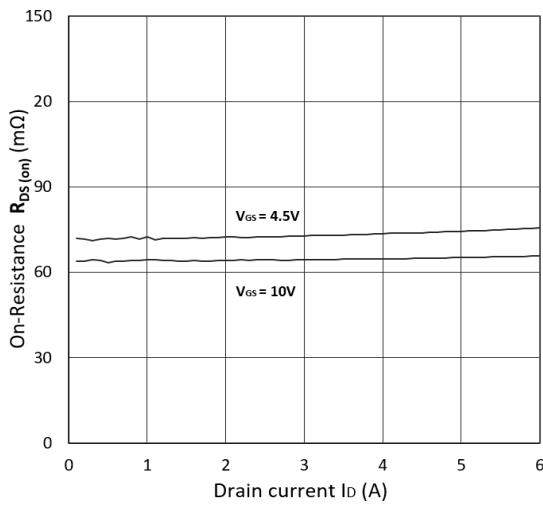
Forward Characteristics of Reverse



Gate Charge Characteristics



$R_{DS(on)}$ vs. V_{GS}



$R_{DS(on)}$ vs. I_D

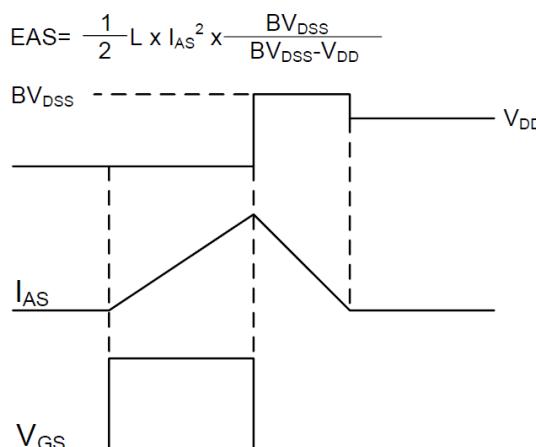
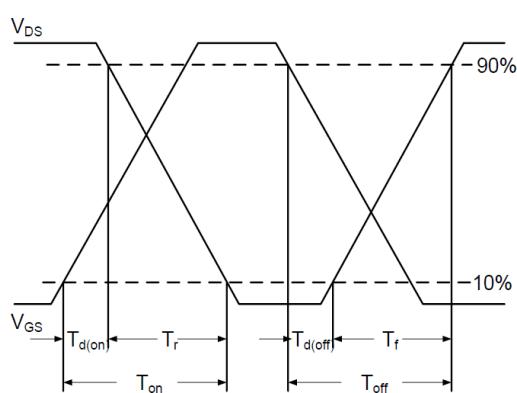
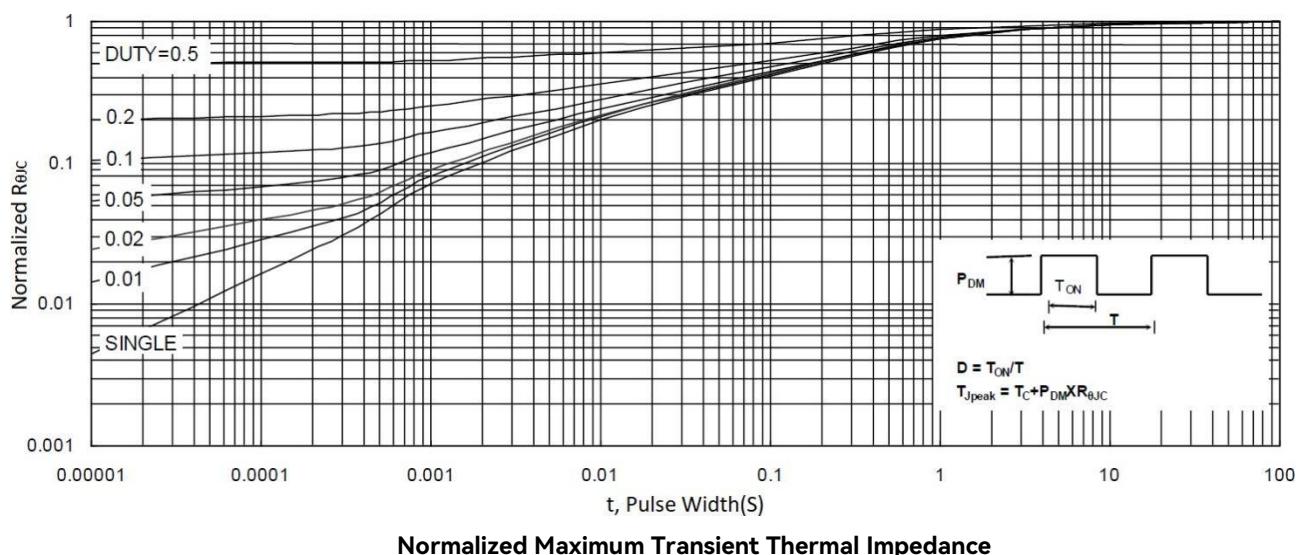
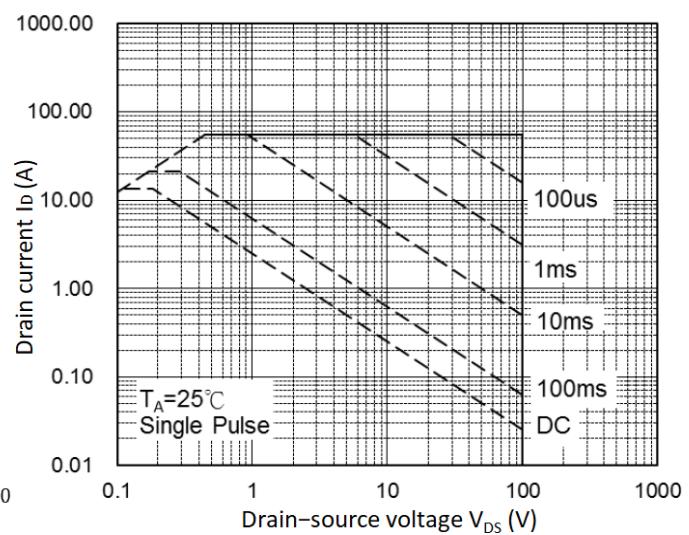
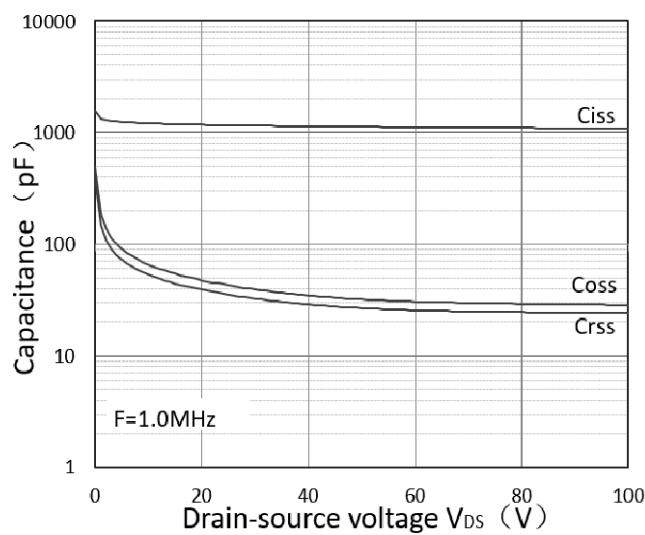


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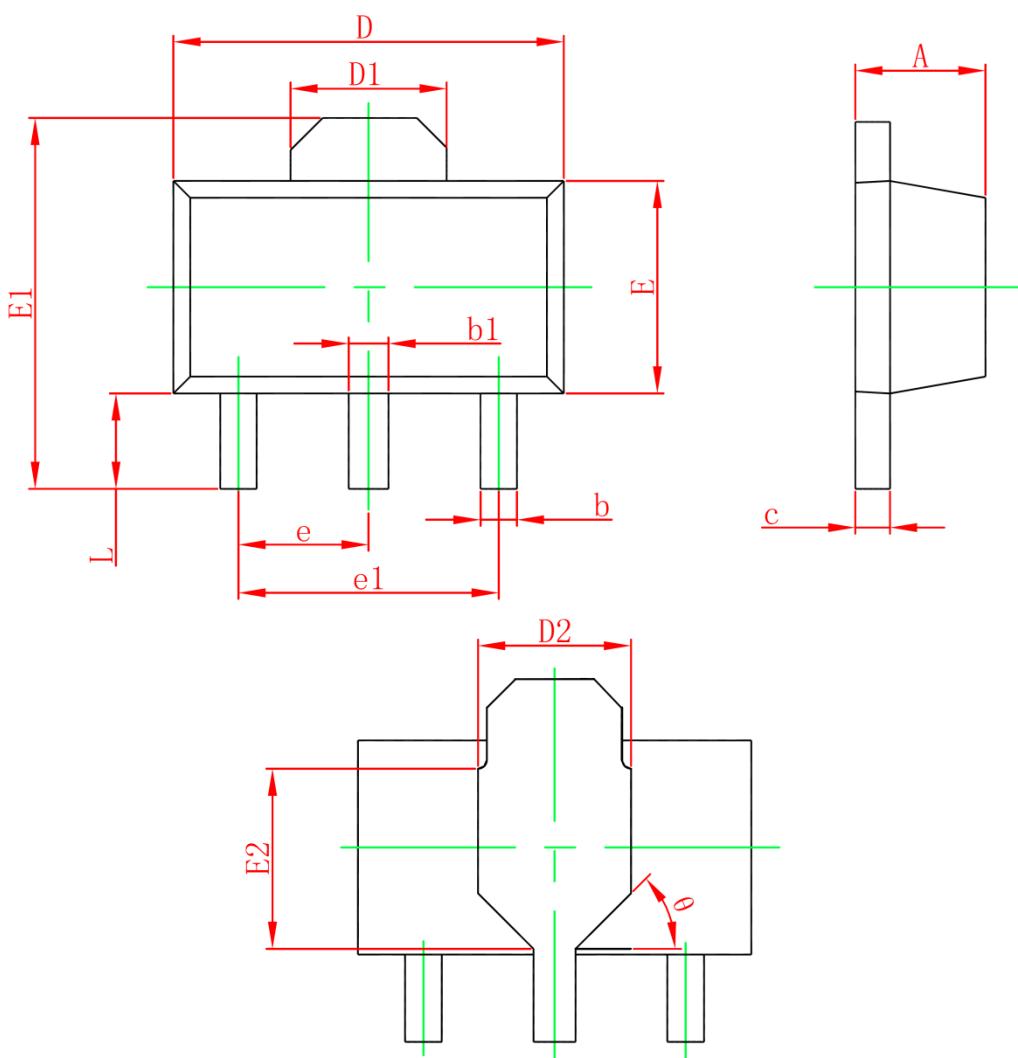
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SOT-89-3L Package

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Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.400	1.600
b	0.320	0.520
b1	0.400	0.580
c	0.350	0.440
D	4.400	4.600
D1	1.550 REF.	
D2	1.750 REF.	
E	2.300	2.600
E1	3.940	4.250
E2	1.900 REF.	
e	1.500 TYP.	
e1	3.000 TYP.	
L	0.900	1.200
θ	45°	